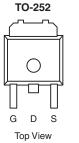


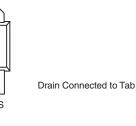
#### SUD50P04-13L

Vishay Siliconix

## P-Channel 40-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)		
- 40	0.013 at V <sub>GS</sub> = - 10 V	- 60 <sup>a</sup>		
	0.022 at V <sub>GS</sub> = - 4.5 V	- 48		

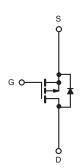




FEATURES

- TrenchFET<sup>®</sup> Power MOSFET
- 175 °C Junction Temperature





Ordering Information: SUD50P04-13L-E3 (Lead (Pb)-free)

P-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> $T_A = 2$	25 °C, unless othe	rwise noted			
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	- 40	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20		
	T <sub>C</sub> = 25 °C	1	- 60 <sup>c</sup>		
Continuous Drain Current <sup>b</sup>	T <sub>C</sub> = 100 °C	I <sub>D</sub>	- 43		
Pulsed Drain Current		I <sub>DM</sub>	- 100		
Continuous Source Current (Diode Conduction)		۱ <sub>S</sub>	- 60 <sup>c</sup>		
Avalanche Current		I <sub>AS</sub>	- 40		
Avalanche Energy,	L = 0.1 mH	E <sub>AS</sub>	80	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	Р	93.7 <sup>b</sup>	w	
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3 <sup>a</sup>	VV	
Operating Junction and Storage Temperature Range	-	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum lumation to Ambianta	t ≤ 10 sec	- R <sub>thJA</sub>	15	18	°C/W
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		40	50	
Maximum Junction-to-Case (Drain)		R <sub>thJC</sub>	1.3	1.8	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. See SOA curve for voltage derating.

b. Calculated based on maximum allowed Junction Temperature. Package limitation current is 50 A.

# SUD50P04-13L

## Vishay Siliconix



Parameter	Symbol	1bol Test Conditions		Тур	Max	Unit	
Static	•	· · · · · · · · · · · · · · · · · · ·					
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 V, I_{D} = -250 \mu A$	- 40			v	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 1.0		- 3.0	v	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -40 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	- 1		- 1		
		$V_{DS}$ = - 40 V, $V_{GS}$ = 0 V, $T_{J}$ = 125 °C			- 50	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 10 V	- 50			Α	
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 30 A		0.0105	0.013	020 Ω	
	r <sub>DS(on)</sub>	$V_{GS}$ = - 10 V, I <sub>D</sub> = - 30 A, T <sub>J</sub> = 125 °C			0.020		
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 20 A		0.017	0.022		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 30 A	15			S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			3120		pF	
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ = - 25 V, $V_{GS}$ = 0 V, f = 1 MHz		440			
Reverse Transfer Capacitance	C <sub>rss</sub>			320			
Gate Resistance	Rg	f = 1 MHz		4.3		Ω	
Total Gate Charge <sup>c</sup>	Qg			63	95		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = -20$ V, $V_{GS} = -10$ V, $I_{D} = -50$ A		13		nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			16			
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			15	25		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = - 20 V, R <sub>L</sub> = 0.4 $\Omega$ I <sub>D</sub> $\cong$ - 50 A, V <sub>GEN</sub> = - 10 V, R <sub>g</sub> = 2.5 $\Omega$		18	30	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			60	90		
Fall Time <sup>c</sup>	t <sub>f</sub>			47	70		
Drain-Source Body Diode Characteristic		1		1	I I		
Pulse Current	I <sub>SM</sub>				- 100		
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = - 50 A, V <sub>GS</sub> = 0 V		- 1.0	- 1.5	V	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 50 A, di/dT = 100 A/μs		36	55	ns	

Notes:

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

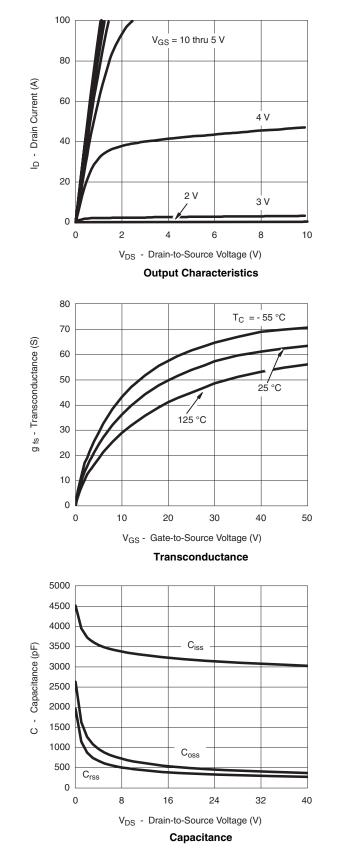
c. Independent of operating temperature.

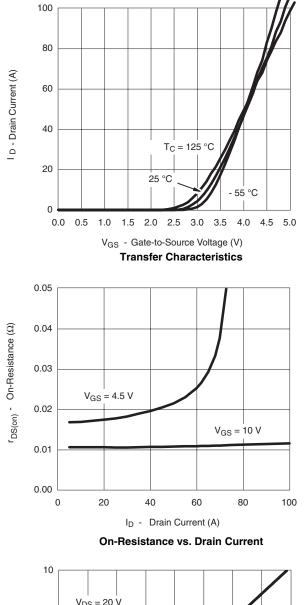
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

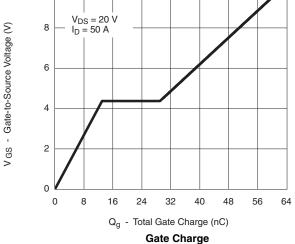


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#### TYPICAL CHARACTERISTICS 25 °C unless noted







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100

. Т<sub>.</sub>ј = 150 °С

Is - Source Current (A)

10

1

0

0.3

0.6

V<sub>SD</sub> - Source-to-Drain Voltage (V)

Source-Drain Diode Forward Voltage

0.9

# SUD50P04-13L

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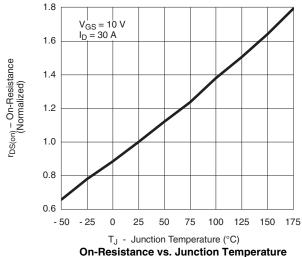
T<sub>J</sub> = 25 <sup>6</sup>C

1.2

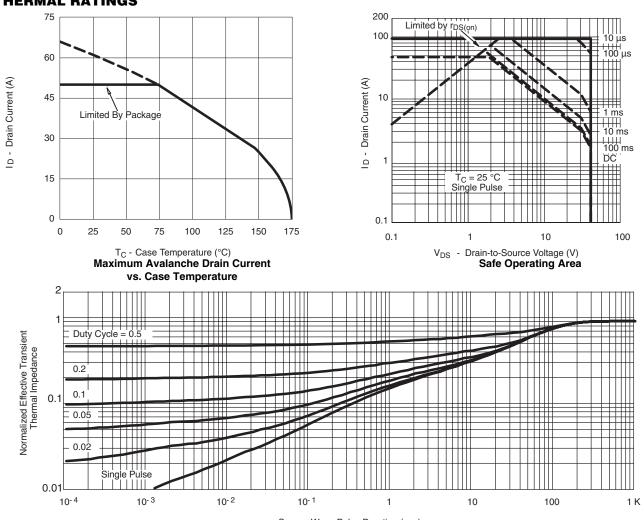
1.5

#### **Vishay Siliconix**

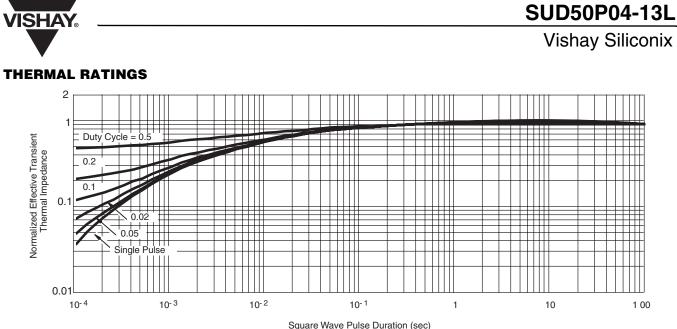
#### TYPICAL CHARACTERISTICS 25 °C unless noted



**THERMAL RATINGS** 



Sauare Wave Pulse Duration (sec) Normalized Thermal Transient Impedance, Junction-to-Ambient



Square Wave Pulse Duration (sec) Normalized Thermal Transient Impedance, Junction-to-Case

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